

NTE319P
Silicon NPN Transistor
VHF Amp ^w/Forward AGC

Absolute Maximum Ratings:

Collector–Emitter Voltage, V_{CEO}	20V
Collector–Base Voltage, V_{CBO}	20V
Emitter–Base Voltage, V_{EBO}	3V
Collector Current, I_C	50mA
Total Power Dissipation ($T_A = +25^\circ\text{C}$), P_T	625mW
Derate above $+25^\circ\text{C}$	5mW/ $^\circ\text{C}$
Operating Junction Temperature, T_J	$+150^\circ\text{C}$
Storage Temperature Range, T_{stg}	-55° to $+150^\circ\text{C}$
Lead Temperature (During Soldering, 1/16" \pm 1/32" from case, 10sec), T_L	$+230^\circ\text{C}$

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}$, $I_E = 0$	20	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}$, $I_C = 0$	3	–	–	V
Collector Cutoff Current	I_{CBO}	$V_{CB} = 20\text{V}$, $I_E = 0$	–	–	50	nA
DC Current Gain	h_{FE}	$I_C = 2\text{mA}$, $V_{CE} = 10\text{V}$	20	80	220	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}$, $I_B = 5\text{mA}$	–	–	2.75	V
Collector–Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 1\text{mA}$, $I_B = 0$	20	–	–	V
Current Gain–Bandwidth Product	f_T	$I_C = 2\text{mA}$, $V_{CE} = 10\text{V}$, $f = 100\text{MHz}$	300	–	500	MHz
Power Gain	G_{pe}	$V_{BE} = 2\text{V}$, $f = 45\text{MHz}$	27	29	–	dB
Capacitance	C_{cb}	$I_E = 0$, $V_{CB} = 10\text{V}$, $f = 1\text{MHz}$	–	0.13	0.22	pF
Noise Figure	NF	$V_{BE} = 2\text{V}$, $f = 45\text{MHz}$	–	2.7	5.0	dB

